

# 2SK2340

## Silicon N-Channel Power F-MOS

### ■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

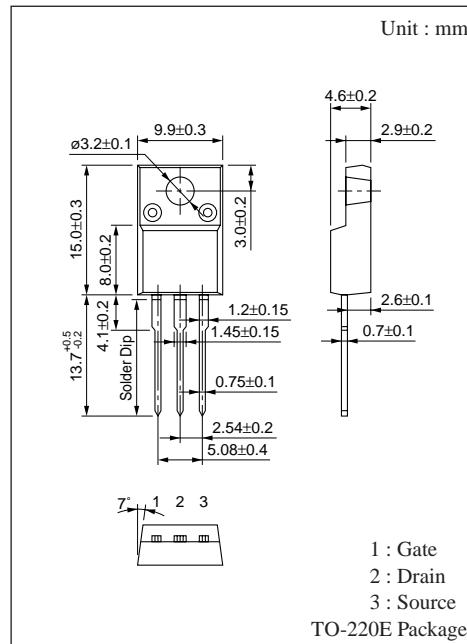
### ■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

### ■ Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	$V_{DSS}$	900	V
Gate-Source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC $I_D$	$\pm 5$	A
	Pulse $I_{DP}$	$\pm 10$	A
Avalanche energy capability	EAS *	45	mJ
Allowable power dissipation	$P_D$	50	W
		2	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

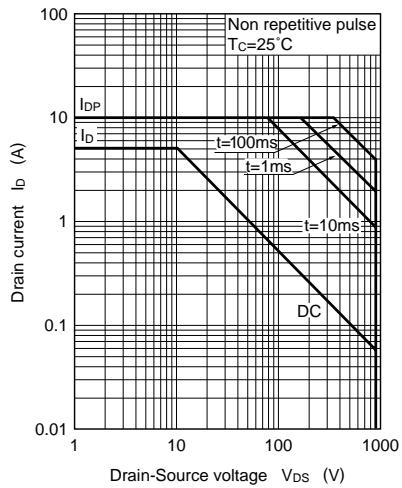
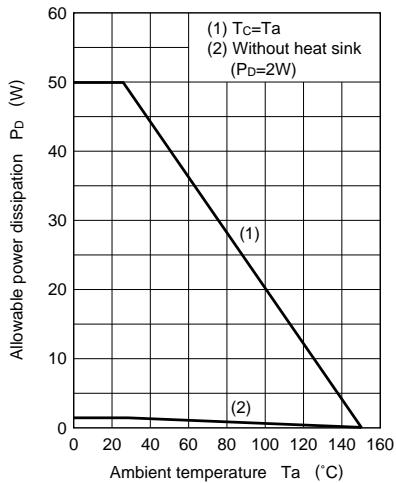
\*  $L = 3.6\text{mH}$ ,  $I_L = 5\text{A}$ , 1 pulse



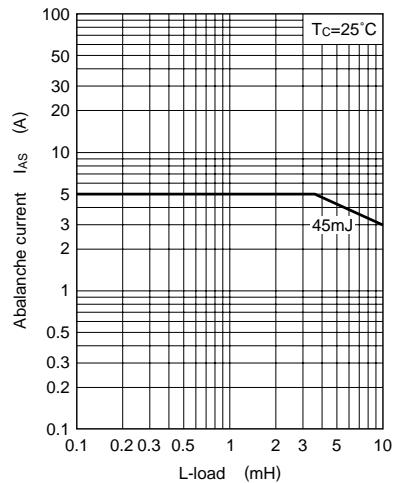
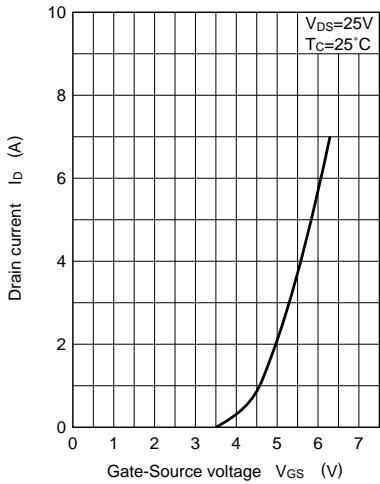
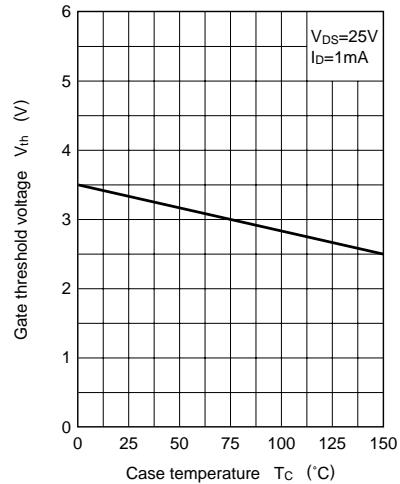
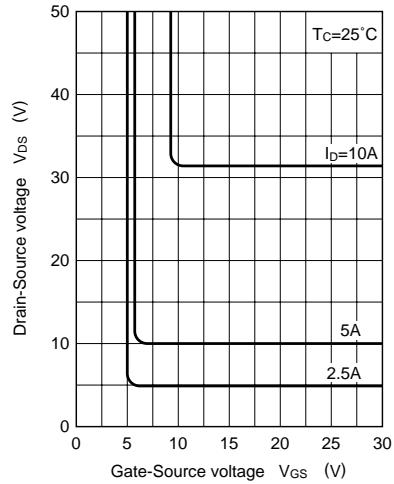
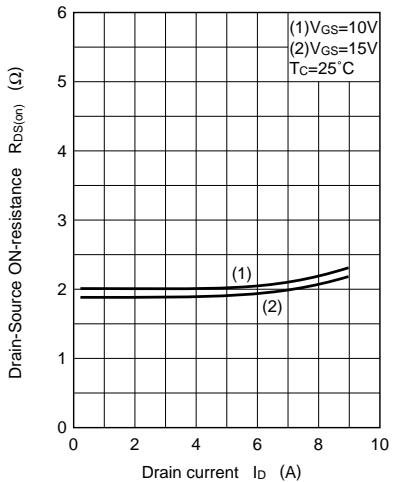
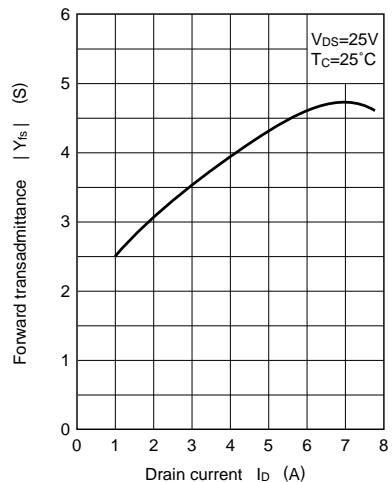
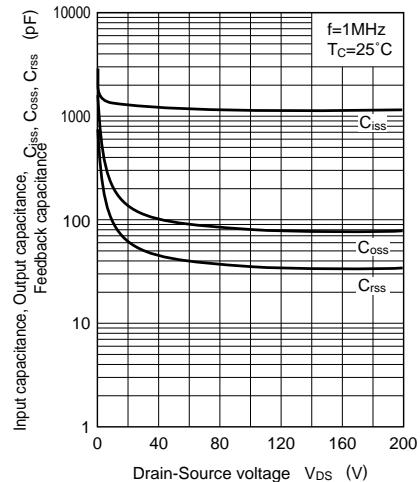
### ■ Electrical Characteristics ( $T_c = 25^\circ\text{C}$ )

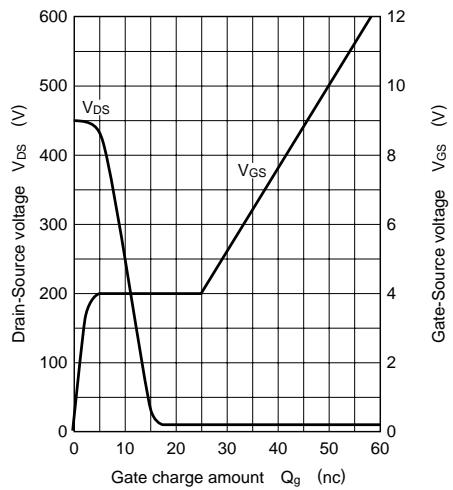
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	$I_{DSS}$	$V_{DS} = 720\text{V}$ , $V_{GS} = 0$			100	$\mu\text{A}$
Gate-Source leakage current	$I_{GSS}$	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0$			$\pm 1$	$\mu\text{A}$
Drain-Source breakdown voltage	$V_{DSS}$	$I_D = 1\text{mA}$ , $V_{GS} = 0$	900			V
Gate threshold voltage	$V_{th}$	$V_{DS} = 25\text{V}$ , $I_D = 1\text{mA}$	2		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_D = 3\text{A}$		2	2.8	$\Omega$
Forward transadmittance	$ Y_{fs} $	$V_{DS} = 25\text{V}$ , $I_D = 3\text{A}$	1.5	3.5		S
Diode forward voltage	$V_{DSF}$	$I_{DR} = 5\text{A}$ , $V_{GS} = 0$			-1.6	V
Input capacitance	$C_{iss}$	$V_{DS} = 20\text{V}$ , $V_{GS} = 0$ , $f = 1\text{MHz}$		1400		pF
Output capacitance	$C_{oss}$			140		pF
Feedback capacitance	$C_{rss}$			60		pF
Turn-on time (delay time)	$t_{d(on)}$	$V_D = 200\text{V}$ , $I_D = 3\text{A}$		30		ns
Rise time	$t_r$			60		ns
Fall time	$t_f$			60		ns
Turn-off time (delay time)	$t_{d(off)}$			170		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				2.5	$^\circ\text{C}/\text{W}$
Channel-Atmosphere heat resistance	$R_{th(ch-a)}$				62.5	$^\circ\text{C}/\text{W}$

Area of safe operation (ASO)

 $P_D - T_a$ 

IAS – L-load

 $I_D - V_{GS}$  $V_{th} - T_c$  $V_{DS} - V_{GS}$  $R_{DS(on)} - I_D$  $|Y_{fs}| - I_D$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$ 

$V_{DS}, V_{GS} - Q_g$  $R_{th} - t_p$ 